DATA SHEET

NEC

NPN SILICON RF TWIN TRANSISTOR

μPA863TS

NPN SILICON RF TRANSISTOR (WITH 2 DIFFERENT ELEMENTS) IN A 6-PIN SUPER LEAD-LESS MINIMOLD

FEATURES

- Low voltage operation
- 2 different built-in transistors (2SC5436, 2SC5800)
  - Q1: Built-in high gain transistor
    - f_T = 12.0 GHz TYP., $|S_{21e}|^2$ = 9.0 dB TYP. @ V_{CE} = 1 V, I_C = 10 mA, f = 2 GHz
  - Q2: Built-in low phase distortion transistor suited for OSC applications
    - f_T = 4.5 GHz TYP., $|S_{21e}|^2$ = 4.0 dB TYP. @ V_{CE} = 1 V, I_C = 5 mA, f = 2 GHz
- 6-pin super lead-less minimold package

BUILT-IN TRANSISTORS

	Q1	Q2
Flat-lead 3-pin thin-type ultra super minimold part No.	2SC5436	2SC5800

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
μPA863TS	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 1 (Q1 Collector), Pin 6 (Q1 Base) face the perforation side of the tape
μPA863TS-T3	10 kpcs/reel	

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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The mark ★ shows major revised points.

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C)

Parameter	Symbol	Ratings		Unit
		Q1	Q2	
Collector to Base Voltage	V_{CBO}	5	9	V
Collector to Emitter Voltage	V_{CEO}	3	5.5	V
Emitter to Base Voltage	V_{EBO}	2	1.5	V
Collector Current	I_C	30	100	mA
Total Power Dissipation	P_{tot} Note	90	110	mW
		130 in 2 elements		
Junction Temperature	T_j	150		°C
Storage Temperature	T_{stg}	–65 to +150		°C

Note Mounted on 1.08 cm^2 × 1.0 mm (t) glass epoxy PCB

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

(1) Q1

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Collector Cut-off Current	I_{CBO}	V_{CB} = 5 V, I_E = 0 mA	–	–	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1 V, I_C = 0 mA	–	–	100	nA
DC Current Gain	h_{FE} Note 1	V_{CE} = 1 V, I_C = 10 mA	70	110	140	–
Gain Bandwidth Product	f_T	V_{CE} = 1 V, I_C = 10 mA, f = 2 GHz	10.0	12.0	–	GHz
Insertion Power Gain	$\lvert S_{21e}\rvert^2$	V_{CE} = 1 V, I_C = 10 mA, f = 2 GHz	7.0	9.0	–	dB
Noise Figure	NF	V_{CE} = 1 V, I_C = 3 mA, f = 2 GHz, $Z_S = Z_{opt}$	–	1.5	2.0	dB
Reverse Transfer Capacitance	C_{re} Note 2	V_{CB} = 0.5 V, I_E = 0 mA, f = 1 MHz	–	0.4	0.7	pF

(2) Q2

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Collector Cut-off Current	I_{CBO}	V_{CB} = 5 V, I_E = 0 mA	–	–	600	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1 V, I_C = 0 mA	–	–	600	nA
DC Current Gain	h_{FE} Note 1	V_{CE} = 1 V, I_C = 5 mA	100	120	145	–
Gain Bandwidth Product (1)	f_T	V_{CE} = 1 V, I_C = 5 mA, f = 2 GHz	3.0	4.5	–	GHz
Gain Bandwidth Product (2)	f_T	V_{CE} = 1 V, I_C = 15 mA, f = 2 GHz	5.0	6.5	–	GHz
Insertion Power Gain (1)	$\lvert S_{21e}\rvert^2$	V_{CE} = 1 V, I_C = 5 mA, f = 2 GHz	3.0	4.0	–	dB
Insertion Power Gain (2)	$\lvert S_{21e}\rvert^2$	V_{CE} = 1 V, I_C = 15 mA, f = 2 GHz	4.5	5.5	–	dB
Noise Figure	NF	V_{CE} = 1 V, I_C = 10 mA, f = 2 GHz, $Z_S = Z_{opt}$	–	1.9	2.5	dB
Reverse Transfer Capacitance	C_{re} Note 2	V_{CB} = 0.5 V, I_E = 0 mA, f = 1 MHz	–	0.6	0.8	pF

Notes 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%

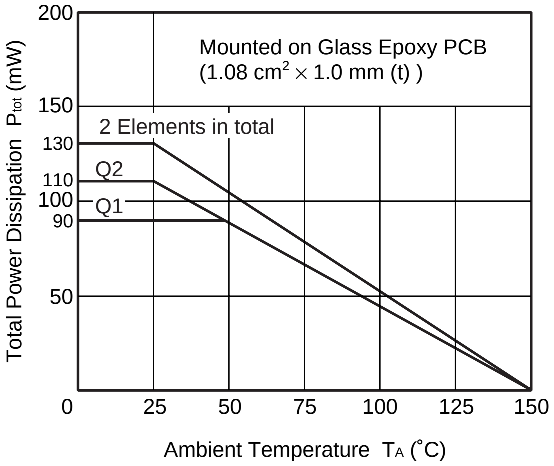
2. Collector to base capacitance when the emitter grounded

h_{FE} CLASSIFICATION

Rank	FB
Marking	xC
h_{FE} Value of Q1	70 to 140
h_{FE} Value of Q2	100 to 145

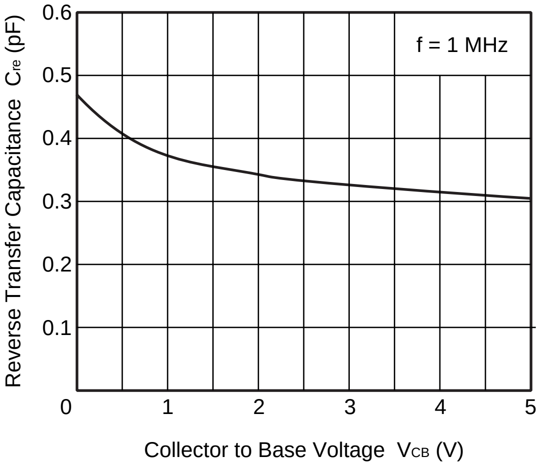
★ TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



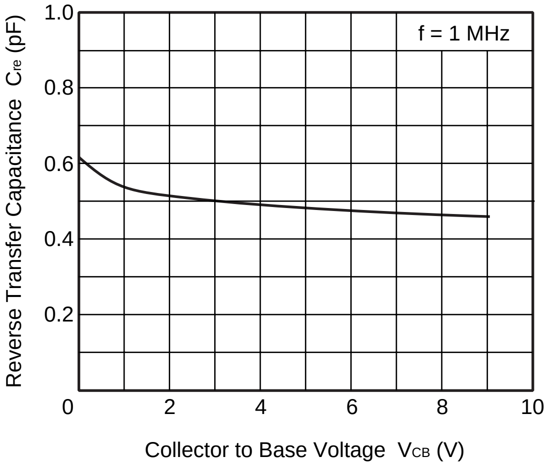
Q1

REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



Q2

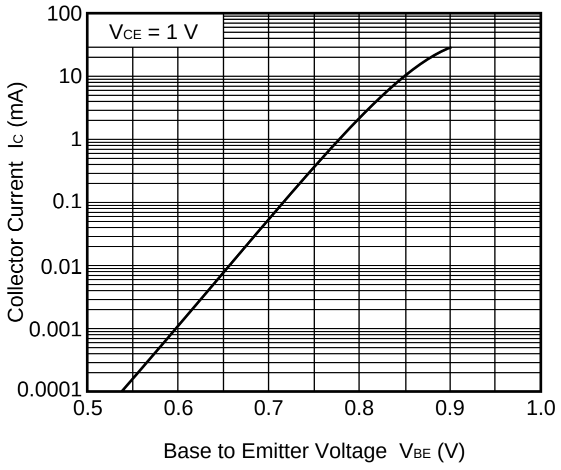
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



Remark The graphs indicate nominal characteristics.

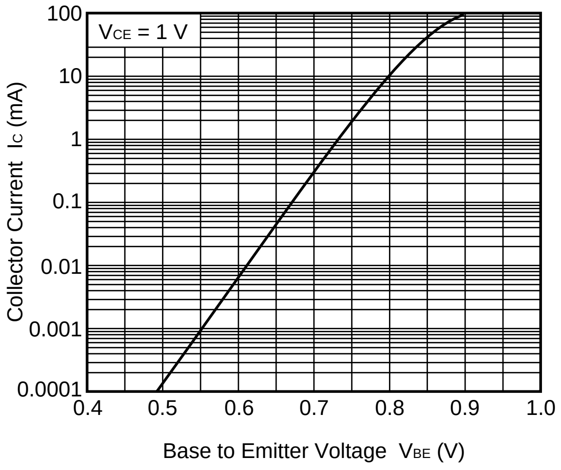
Q1

COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE

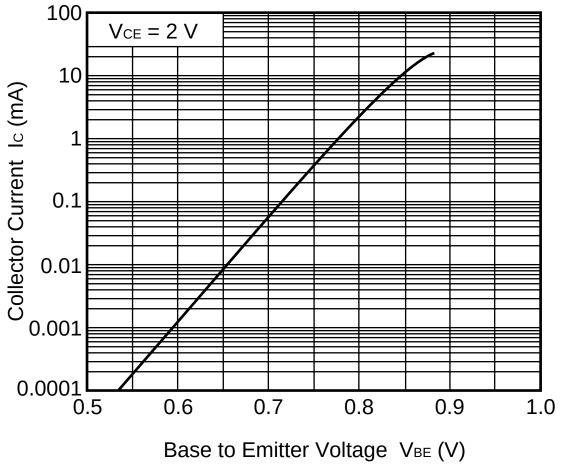


Q2

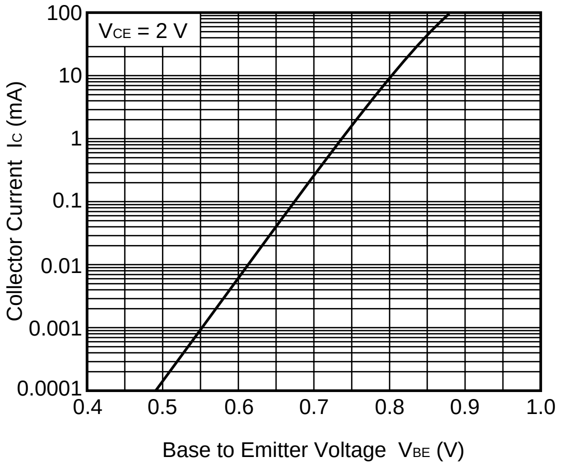
COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



Remark The graphs indicate nominal characteristics.